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October 2013

### FDMC8032L

# Dual N-Channel PowerTrench<sup>®</sup> MOSFET 40 V, 7 A, 20 m $\Omega$

#### **Features**

- Max  $r_{DS(on)} = 20 \text{ m}\Omega$  at  $V_{GS} = 10 \text{ V}$ ,  $I_D = 7 \text{ A}$
- Max  $r_{DS(on)}$  = 27 m $\Omega$  at  $V_{GS}$  = 4.5 V,  $I_D$  = 6 A
- Low Inductance Packaging Shortens Rise/Fall Times
- Lower Switching Losses
- 100% Rg Tested
- Termination is Lead-free and RoHS Compliant

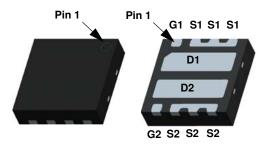


#### **General Description**

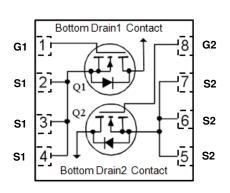
This device includes two 40V N-Channel MOSFETs in a dual Power 33 (3 mm X 3 mm MLP) package. The package is enhanced for exceptional thermal performance.

#### **Applications**

- Battery Protection
- Load Switching
- Point of Load



Power 33



#### **MOSFET Maximum Ratings** T<sub>A</sub> = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
$V_{DS}$	Drain to Source Voltage			40	V
$V_{GS}$	Gate to Source Voltage			±20	V
	Drain Current -Continuous	T <sub>C</sub> = 25 °C		20	
I <sub>D</sub>	-Continuous	T <sub>A</sub> = 25 °C	(Note 1a)	7	Α
	-Pulsed		(Note 4)	50	
E <sub>AS</sub>	Single Pulse Avalanche Energy		(Note 3)	13	mJ
D	Power Dissipation	T <sub>C</sub> = 25 °C		12	W
$P_{D}$	Power Dissipation	T <sub>A</sub> = 25 °C	(Note 1a)	1.9	VV
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Tempera	ture Range		-55 to +150	°C

#### **Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance, Junction to Case	9.7	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a	) 65	C/VV

#### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC8032L	FDMC8032L	Power 33	13 "	12 mm	3000 units

### **Electrical Characteristics** $T_J = 25 \, ^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	40			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, referenced to 25 °C		23		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 32 V, V <sub>GS</sub> = 0 V			1	μΑ
$I_{GSS}$	Gate to Source Leakage Current, Forward	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA

#### **On Characteristics**

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	1.0	1.8	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, referenced to 25 °C		-5		mV/°C
	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 7 \text{ A}$		16	20	
rpo()		$V_{GS} = 4.5 \text{ V}, I_D = 6 \text{ A}$		21	27	mΩ
r <sub>DS(on)</sub> Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 7 \text{ A}$ $T_J = 125 \text{ °C}$		23	29	11122	
9 <sub>FS</sub>	Forward Transconductance	$V_{DD} = 5 \text{ V}, \ I_{D} = 7 \text{ A}$		27		S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 00.V.V 0.V		513	720	рF
Coss	Output Capacitance	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$ f = 1MHz		137	195	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 111112		9.3	15	pF
$R_g$	Gate Resistance		0.1	2.6	3.6	Ω

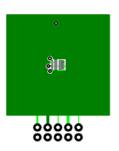
#### **Switching Characteristics**

	•				
t <sub>d(on)</sub>	Turn-On Delay Time		5.5	11	ns
t <sub>r</sub>	Rise Time	V <sub>DD</sub> = 20 V, I <sub>D</sub> = 7 A	1.2	10	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$	13	24	ns
t <sub>f</sub>	Fall Time		1.3	10	ns
0	Total Gate Charge	V <sub>GS</sub> = 0 V to 10 V	7.6	11	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0 \text{ V to } 4.5 \text{ V}$ $V_{DD} = 20 \text{ V}$	3.6	5.1	nC
$Q_{gs}$	Gate to Source Charge	I <sub>D</sub> = 7 A	1.5		nC
Q <sub>ad</sub>	Gate to Drain "Miller" Charge		1.0		nC

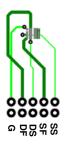
#### **Drain-Source Diode Characteristics**

V <sub>SD</sub> Source to Drain Diode Forward Voltage	Source to Drain Diode Ferward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 7 \text{ A}$	(Note 2)	0.85	1.3	V
	$V_{GS} = 0 \text{ V}, I_{S} = 1.4 \text{ A}$	(Note 2)	0.75	1.2	, v	
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 7 A, di/dt = 100 A/μs		16	29	ns
Q <sub>rr</sub>	Reverse Recovery Charge			3.9	10	nC

<sup>1.</sup>  $R_{\theta JA}$  is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a. 65 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b. 155 °C/W when mounted on a minimum pad of 2 oz copper

- 2. Pulse Test: Pulse Width < 300  $\mu s,$  Duty cycle < 2.0 %.
- 3.  $E_{AS}$  of 13 mJ is based on starting  $T_J$  = 25 °C, L = 3 mH,  $I_{AS}$  = 3 A,  $V_{DD}$  = 40 V,  $V_{GS}$  = 10 V. 100% tested at L = 0.1 mH,  $I_{AS}$  = 11 A. 4. Pulse Id refers to Figure.11 Forward Bias Safe Operation Area.

### Typical Characteristics T<sub>J</sub> = 25 °C unless otherwise noted

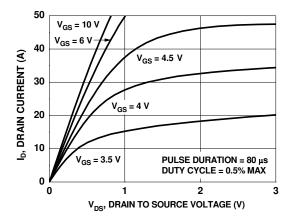


Figure 1. On-Region Characteristics

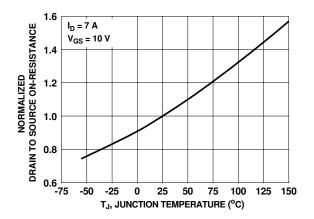


Figure 3. Normalized On-Resistance vs Junction Temperature

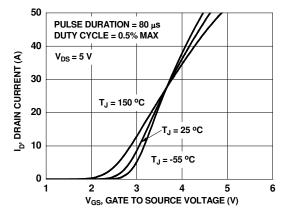


Figure 5. Transfer Characteristics

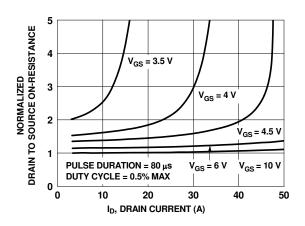


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

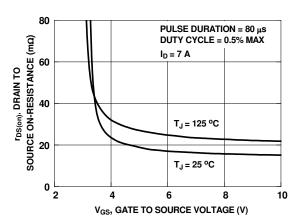


Figure 4. On-Resistance vs Gate to Source Voltage

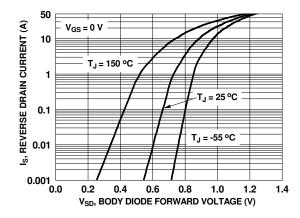


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

### Typical Characteristics $T_J = 25$ °C unless otherwise noted

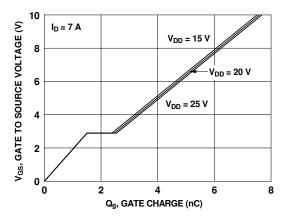


Figure 7. Gate Charge Characteristics

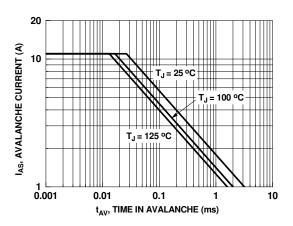


Figure 9. Unclamped Inductive Switching Capability

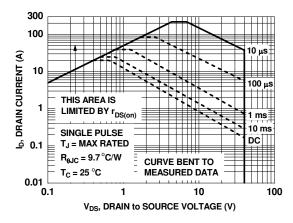


Figure 11. Forward Bias Safe Operating Area

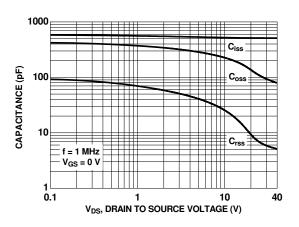


Figure 8. Capacitance vs Drain to Source Voltage

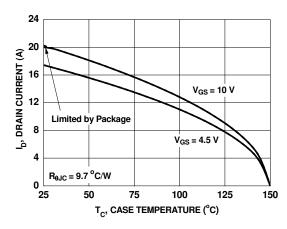


Figure 10. Maximum Continuous Drain Current vs Case Temperature

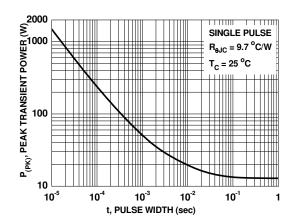


Figure 12. Single Pulse Maximum Power Dissipation

## Typical Characteristics T<sub>J</sub> = 25 °C unless otherwise noted

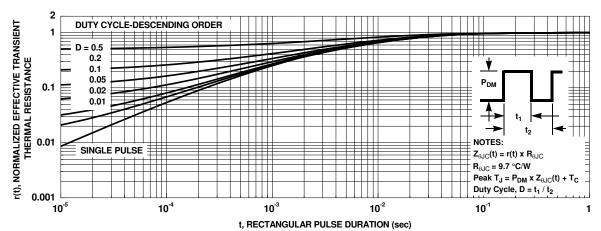
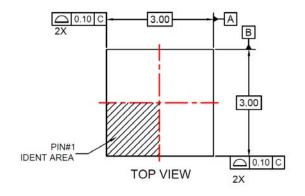
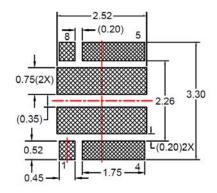
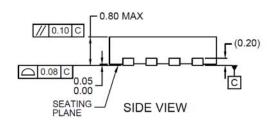


Figure 13. Transient Thermal Response Curve

### **Dimensional Outline and Pad Layout**



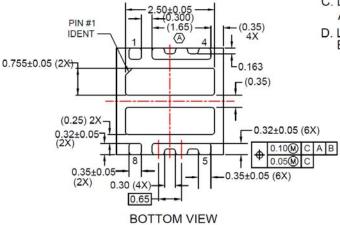




RECOMMENDED LAND PATTERN

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